## N-Channel 300-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

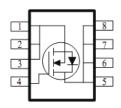
Typical A	Applicati	ions:
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- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$			
300	600 @ V <sub>GS</sub> = 10V	2.4		
	900 @ V <sub>GS</sub> = 5.5V	1.9		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			300	V		
Gate-Source Voltage	$V_{GS}$	±20	V			
Continuous Dusin Commenta	T <sub>A</sub> =25°C		2.4	А		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70°C		1.9			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	10				
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	6.2	Α			
Device Dissinction 8	T <sub>A</sub> =25°C		5	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C		3.2	V V		
Operating Junction and Storage Temperature Range			-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IN <sub>θ</sub> JΑ	65	C/VV			

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

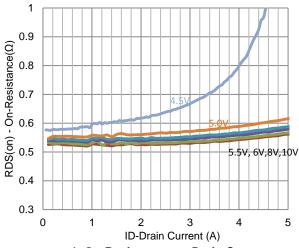
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , ID = 250 uA	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	uA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 240 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = 240 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 2.0 \text{ A}$			600	mΩ	
Dialii-Source Off-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 5.5 \text{ V}, I_D = 1.6 \text{ A}$			900	11122	
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 2.0 \text{ A}$		10		S	
Diode Forward Voltage	$V_{SD}$	$I_S = 3.1 \text{ A}, V_{GS} = 0 \text{ V}$		0.77		V	
		Dynamic					
Total Gate Charge	$Q_g$			14.4			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 120 \text{ V}, V_{GS} = 10 \text{ V}, ID = 2.0 \text{ A}$		3.9		nC	
Gate-Drain Charge	$Q_{gd}$			3.6			
Turn-On Delay Time	t <sub>d(on)</sub>			12.2			
Rise Time	t <sub>r</sub>	$V_{DD}$ = 120 V, $R_L$ = 60 $\Omega$ , $I_D$ = 2.0 A,		9		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		32		ns	
Fall Time	t <sub>f</sub>			20			
Input Capacitance	C <sub>iss</sub>			1092			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		90		pF	
Reverse Transfer Capacitance	$C_{rss}$			52			

#### Notes

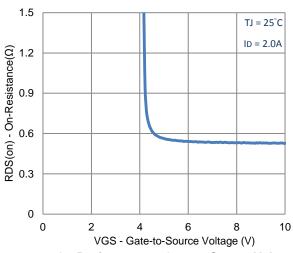
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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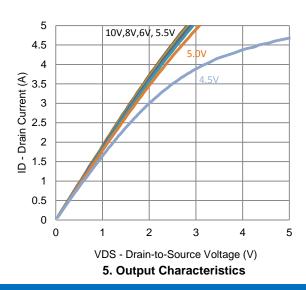
## **Typical Electrical Characteristics**

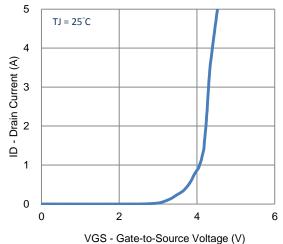


#### 1. On-Resistance vs. Drain Current

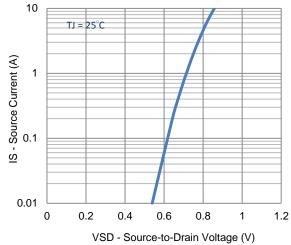


3. On-Resistance vs. Gate-to-Source Voltage

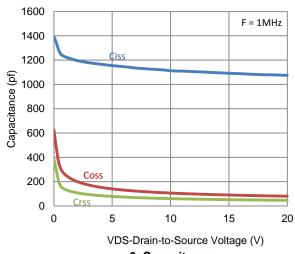




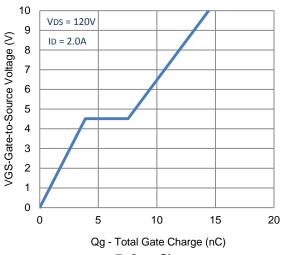
2. Transfer Characteristics

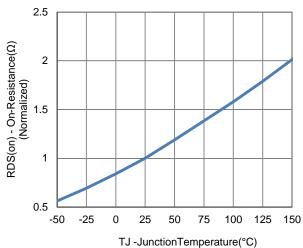


4. Drain-to-Source Forward Voltage



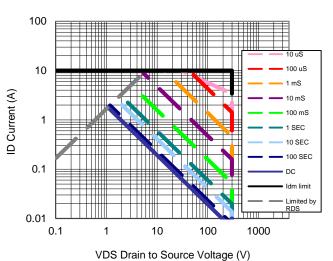
## **Typical Electrical Characteristics**

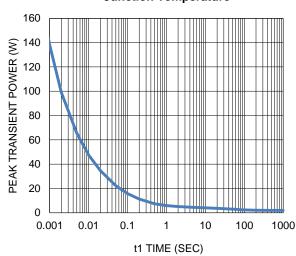




7. Gate Charge

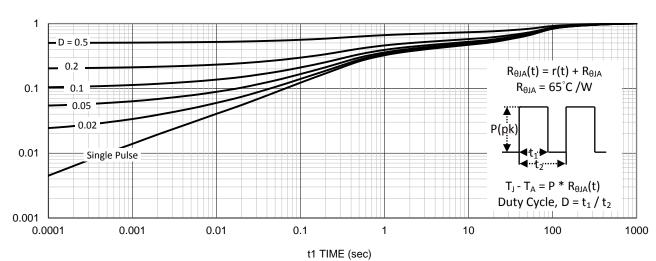






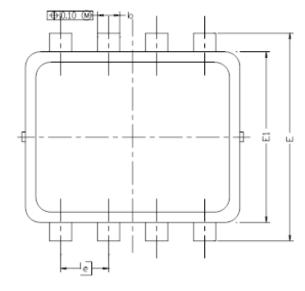
9. Safe Operating Area

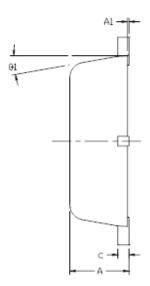
10. Single Pulse Maximum Power Dissipation

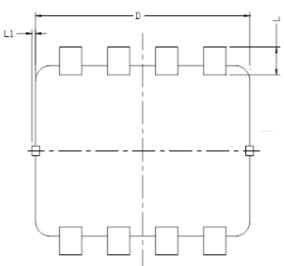


11. Normalized Thermal Transient Junction to Ambient

# Package Information







DIM.	MILLIMETERS			INCHES			
DIM.	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.700	0.80	0,900	0.0276	0.0315	0.0354	
A1	0.00		0.05	0,000		0.002	
b	0,24	0,30	0,35	0.009	0.012	0.014	
_	0.08	0.152	0.25	0.003	0.006	0.010	
D	2,90 BSC			0.114 BSC			
E	2.80 BSC			0.110 BSC			
E1	2.30 BSC			0.091 BSC			
9	0	.65 BS	С	0.026 BSC			
L	0.20	0.375	0.450	0.008	0.0148	0.0177	
L1	0		0.100	0		0.004	
91	0	10	12	0	10	12	